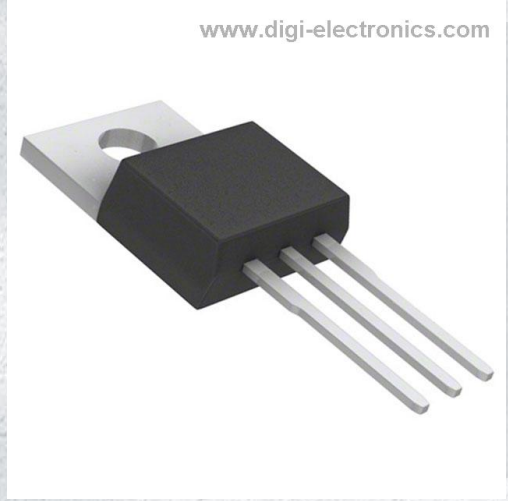
FDP047N08 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	FDP047N08-DG
Manufacturer	onsemi
Manufacturer Product Number	FDP047N08
Description	MOSFET N-CH 75V 164A TO220-3
Detailed Description	N-Channel 75 V 164A (Tc) 268W (Tc) Through Hole TO-220-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FDP047N08	onsemi
Series:	Product Status:
PowerTrench®	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
75 V	164A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	4.7mOhm @ 80A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4.5V @ 250µA	152 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	9415 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	268W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
TO-220-3	TO-220-3
Base Product Number:	
FDP047	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

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FAIRCHILD SEMICONDUCTOR®

November 2013

FDP047N08

N-Channel PowerTrench® MOSFET

75 V, 164 A, 4.7 mΩ

Features

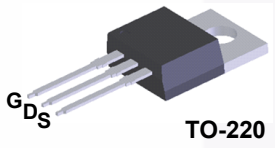
- $R_{DS(on)}$ = 3.8 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 80 A
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

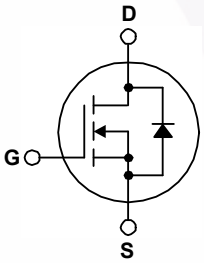
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies



TO-220



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDP047N08	Unit
V_{DSS}	Drain to Source Voltage			75	V
V_{GSS}	Gate to Source Voltage			±20	V
I_D	Drain Current	- Continuous (T_C = 25°C)		164*	A
		- Continuous (T_C = 100°C)		116*	A
I_{DM}	Drain Current	- Pulsed	(Note 1)	656	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	670	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	6.0	V/ns
P_D	Power Dissipation	(T_C = 25°C)		268	W
		- Derate Above 25°C		1.79	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 80A.

Thermal Characteristics

Symbol	Parameter	FDP047N08	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.56	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP047N08	FDP047N08	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V, $T_C = 25^oC$	75	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25^oC	-	0.02	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 75 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 75 V, $T_C = 150^oC$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 80 A	-	3.7	4.7	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 80 A	-	150	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	-	7080	9415	pF
C_{oss}	Output Capacitance		-	870	1155	pF
C_{rss}	Reverse Transfer Capacitance		-	410	615	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 37.5 V, I_D = 80 A, R_G = 25 Ω, V_{GS} = 10 V (Note 4)	-	100	210	ns
t_r	Turn-On Rise Time		-	147	304	ns
$t_{d(off)}$	Turn-Off Delay Time		-	220	450	ns
t_f	Turn-Off Fall Time		-	114	238	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 60 V, I_D = 80 A, V_{GS} = 10 V (Note 4)	-	117	152	nC
Q_{gs}	Gate to Source Gate Charge		-	37	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	32	-	nC
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	164	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	656	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 80 A	-	-	1.25	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 80 A, dI_F/dt = 100 A/μs	-	45	-	ns
Q_{rr}	Reverse Recovery Charge		-	66	-	nC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. L = 0.21 mH, I_{AS} = 80 A, V_{DD} = 50 V, R_G = 25 Ω, starting $T_J = 25°C$.
3. $I_{SD} \le 80$ A, di/dt ≤ 200 A/μs, $V_{DD} \le BV_{DSS}$, starting $T_J = 25°C$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

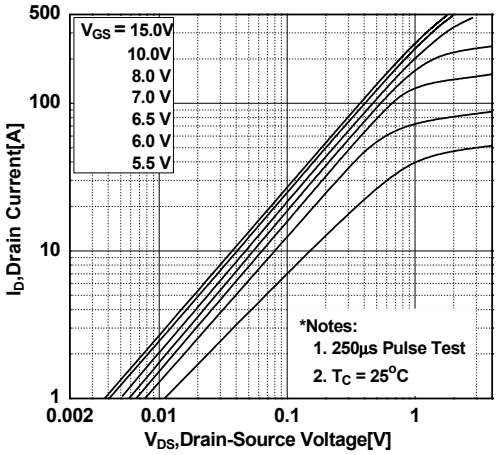


Figure 2. Transfer Characteristics

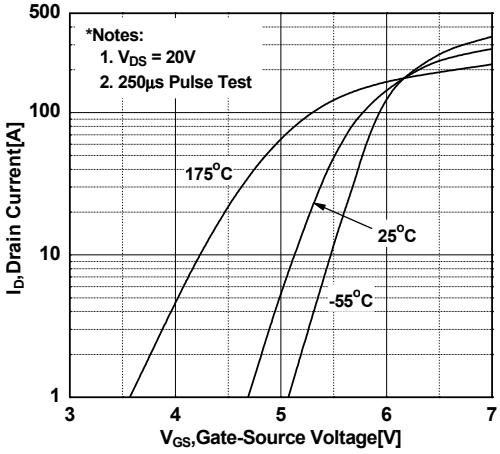


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

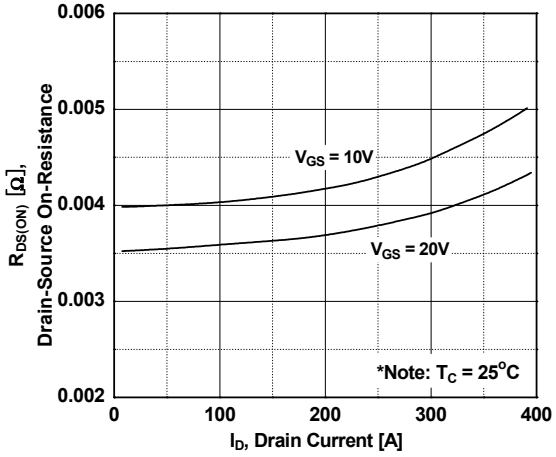


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

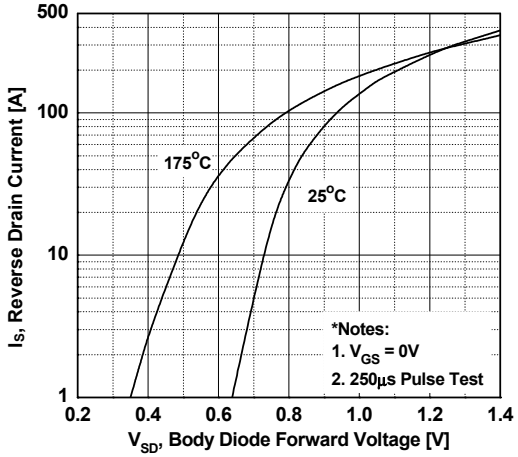


Figure 5. Capacitance Characteristics

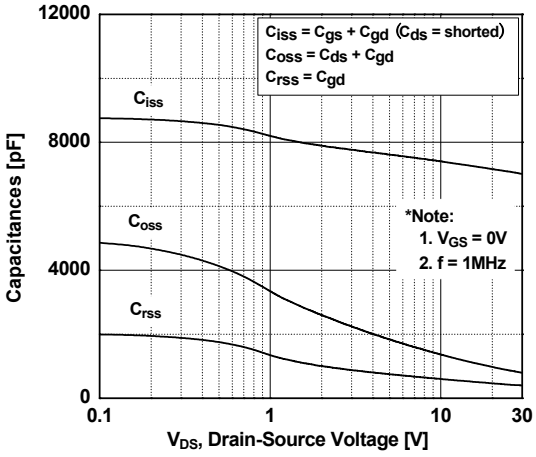
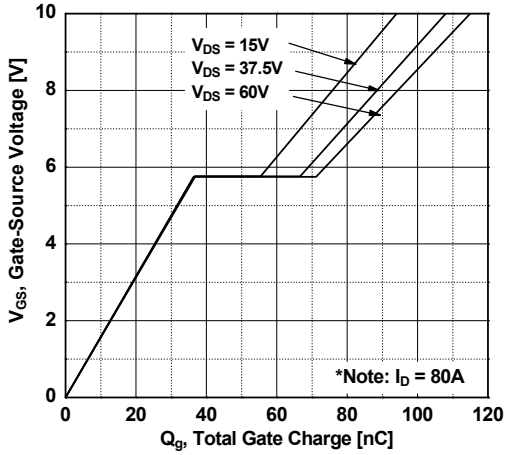


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

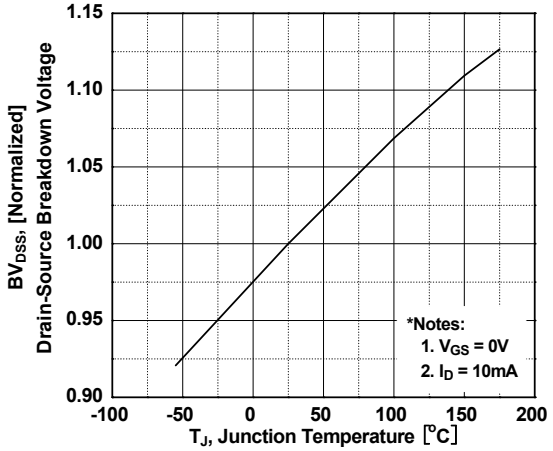


Figure 8. On-Resistance Variation vs. Temperature

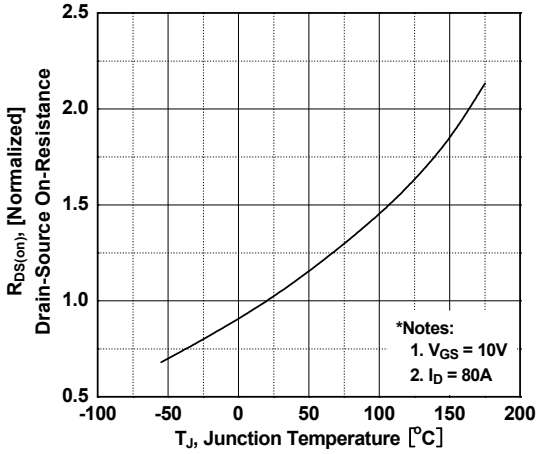


Figure 9. Maximum Safe Operating Area

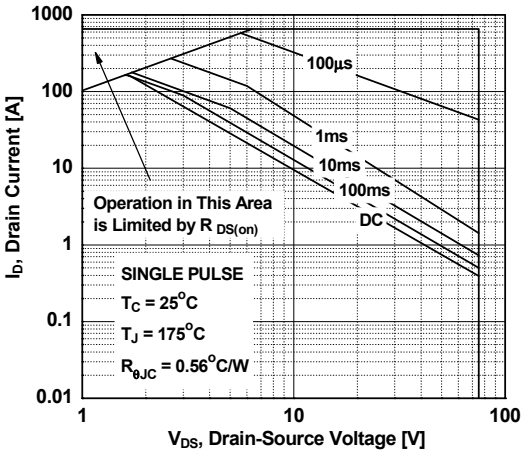


Figure 10. Maximum Drain Current vs. Case Temperature

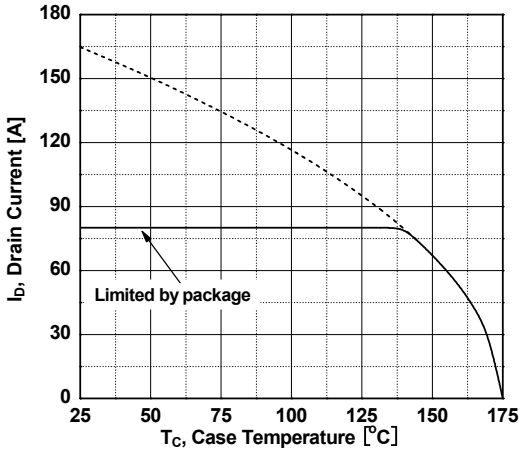
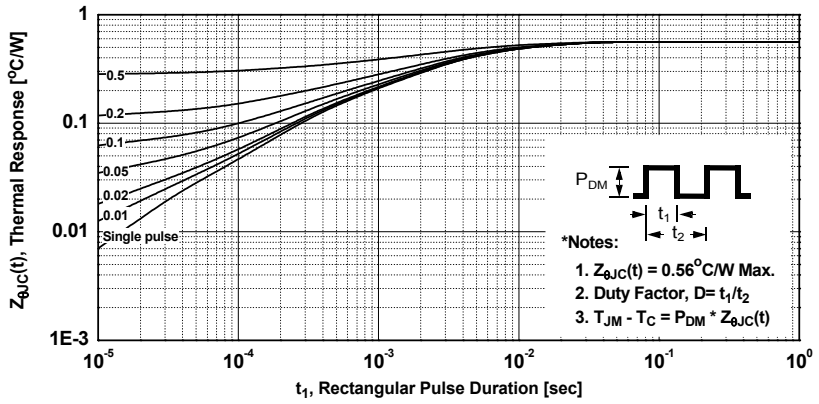


Figure 11. Transient Thermal Response Curve



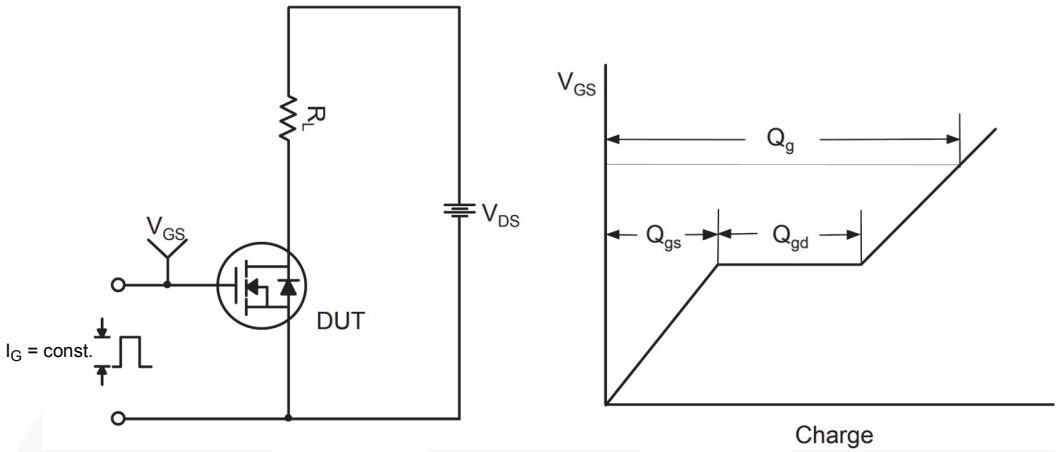


Figure 12. Gate Charge Test Circuit & Waveform

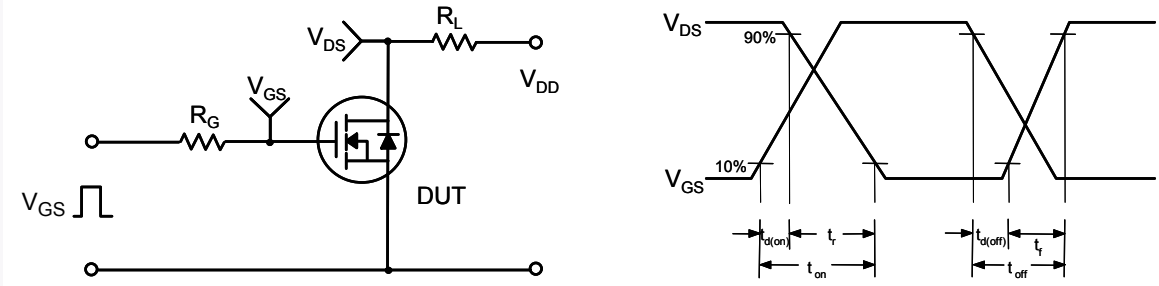


Figure 13. Resistive Switching Test Circuit & Waveforms

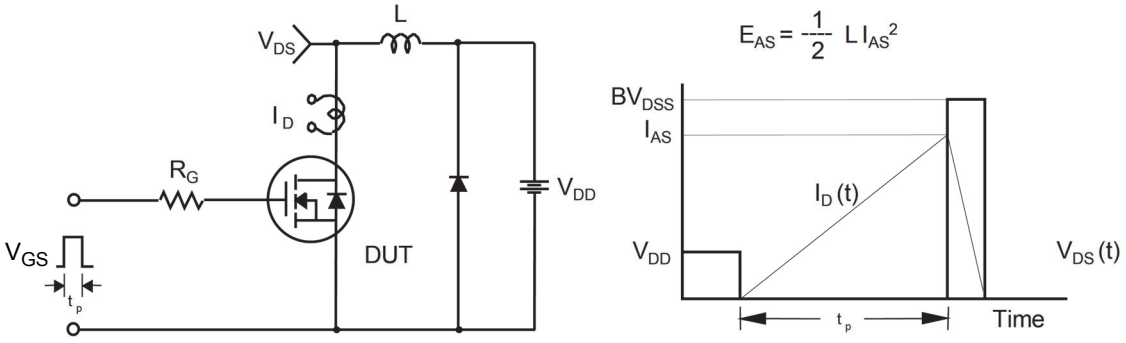


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

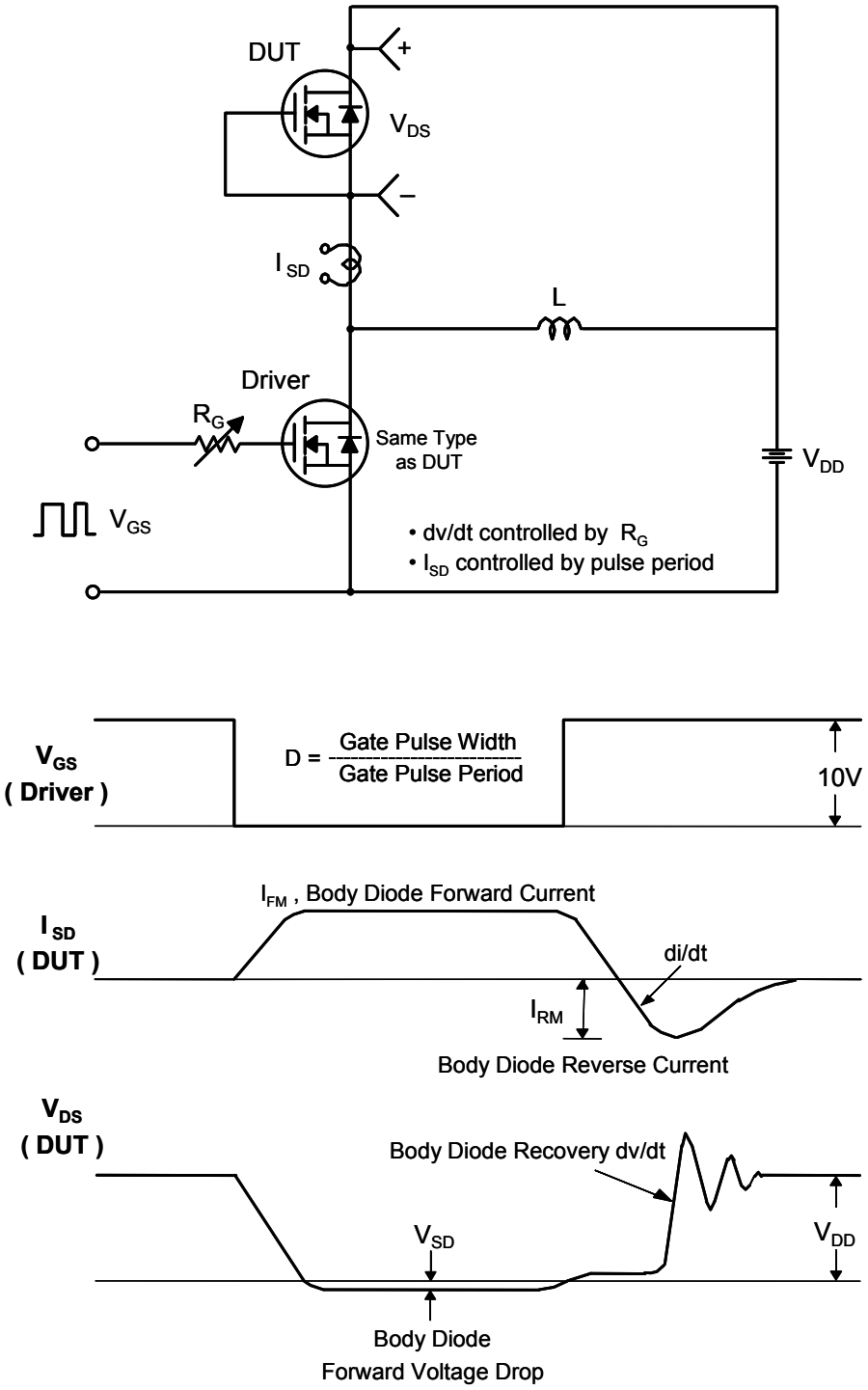


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

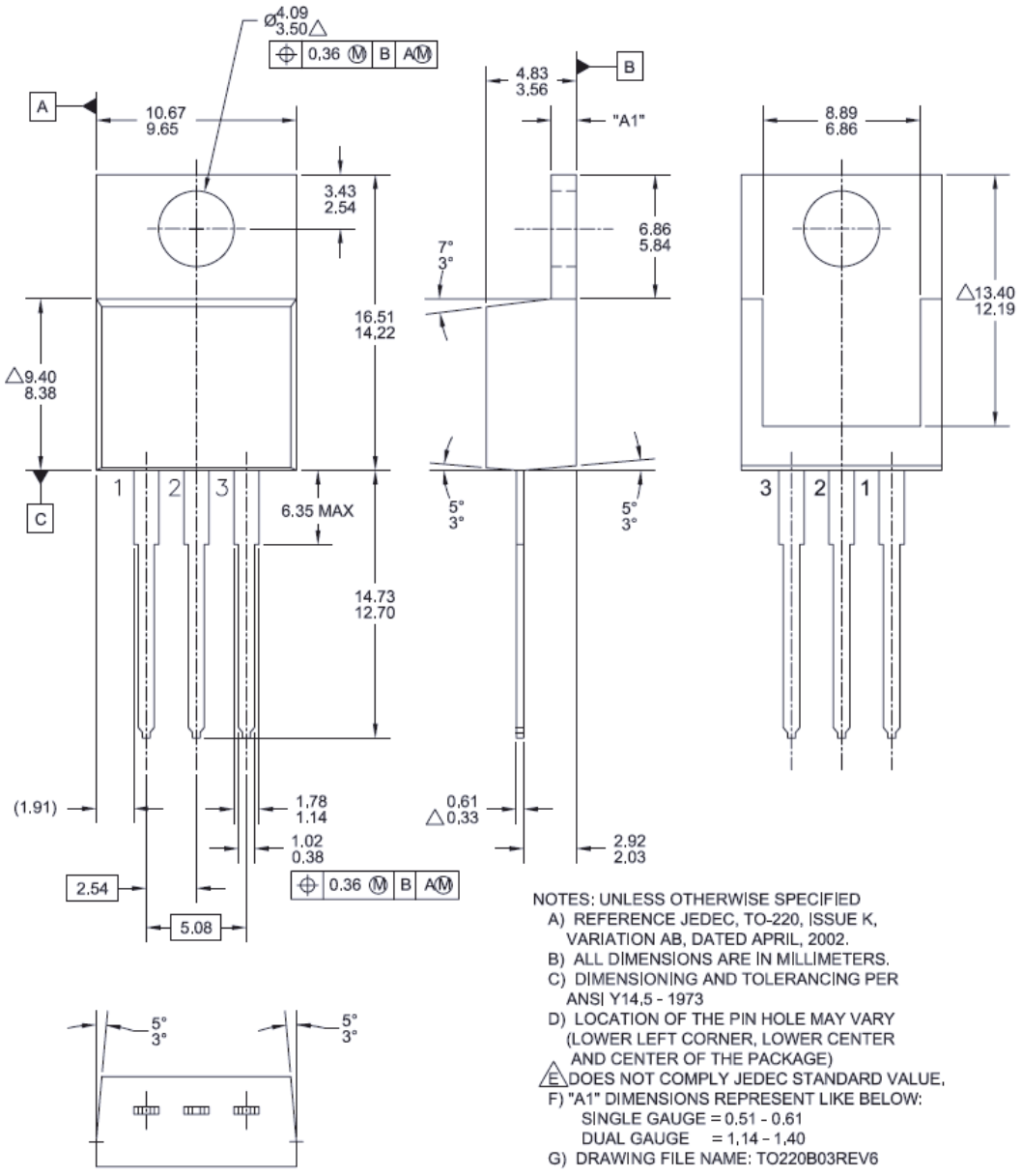


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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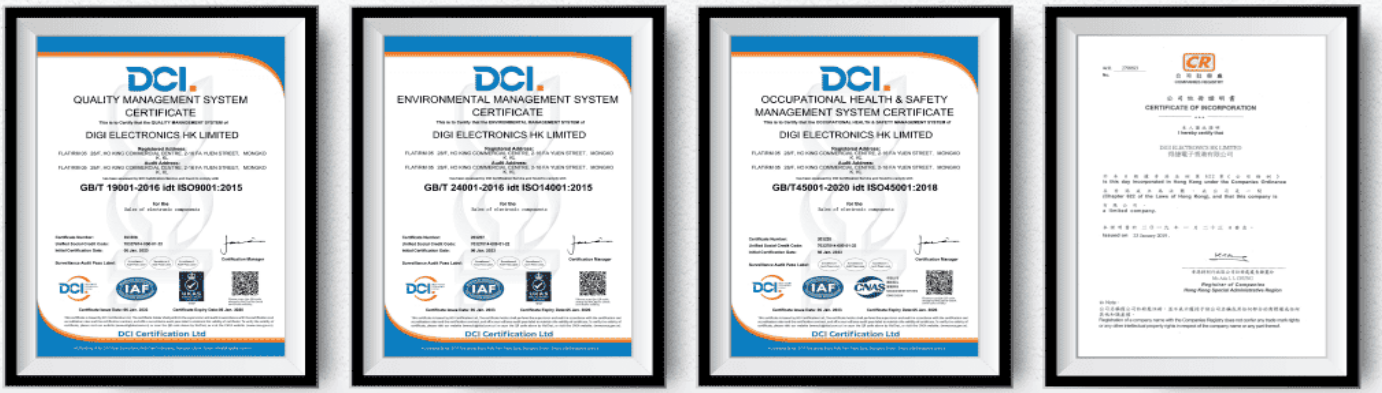

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